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RFP2N08, RFP2N10

2A, 80V and 100V, 1.05 Ohm,
N-Channel Power MOSFETs

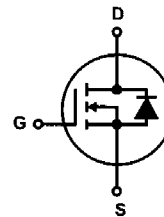
Features

- 2A, 80V and 100V
- $r_{DS(ON)}$ 1.05 Ω
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Related Literature

Description

These are N-channel enhancement mode silicon gate power field effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Symbol



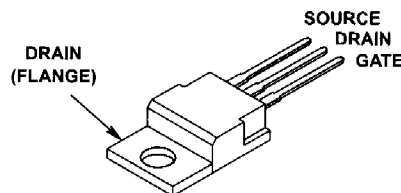
Ordering Information

PART NUMBER	PACKAGE	BRAND
RFP2N08	TO-220AB	RFP2N08
RFP2N10	TO-220AB	RFP2N10

NOTE: When ordering, use entire part number.

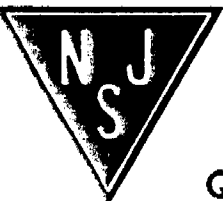
Packaging

JEDEC TO-220AB



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFP2N08	RFP2N10	UNITS	
Drain to Source Voltage (Note 1)	V_{DSS}	80	100	V
Drain to Gate Voltage ($R_{GS} = 1M\Omega$) (Note 1)	V_{DGR}	80	100	V
Continuous Drain Current	I_D	2	2	A
Pulsed Drain Current (Note 3)	I_{DM}	5	5	A
Gate to Source Voltage	V_{GS}	± 20	± 20	V
Maximum Power Dissipation	P_D	25	25	W
Linear Derating Factor		0.2	0.2	W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$
Maximum Temperature for Soldering				
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0$	100	-	-	V
RFP2N10			80	-	-	V
RFP2N08						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 8)	2	-	4	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = \text{Rated } BV_{DSS}, T_C = 25^\circ\text{C}$	-	-	1	μA
		$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, T_C = 125^\circ\text{C}$	-	-	25	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$	-	-	± 100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 2\text{A}, V_{GS} = 10\text{V}$ (Figures 6, 7)	-	-	1.05	Ω
Drain to Source On Voltage (Note 2)	$V_{DS(ON)}$	$I_D = 2\text{A}, V_{GS} = 10\text{V}$	-	-	2.1	V
Turn-On Delay Time	$t_{d(ON)}$	$I_D = 1\text{A}, V_{DD} = 50\text{V}, R_G = 50\Omega, R_L = 25\Omega, V_{GS} = 10\text{V}$ (Figures 10, 11, 12)	-	17	25	ns
Rise Time	t_r		-	30	45	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	30	45	ns
Fall Time	t_f		-	17	25	ns
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ (Figure 9)	-	-	200	pF
Output Capacitance	C_{OSS}		-	-	80	pF
Reverse-Transfer Capacitance	C_{RSS}		-	-	25	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	5	$^\circ\text{C/W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	$I_{SD} = 2\text{A}$	-		1.4	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 2\text{A}, dI_{SD}/dt = 50\text{A}/\mu\text{s}$	-	100	-	ns

NOTES:

2. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Repetitive rating: pulse width limited by maximum junction temperature.